

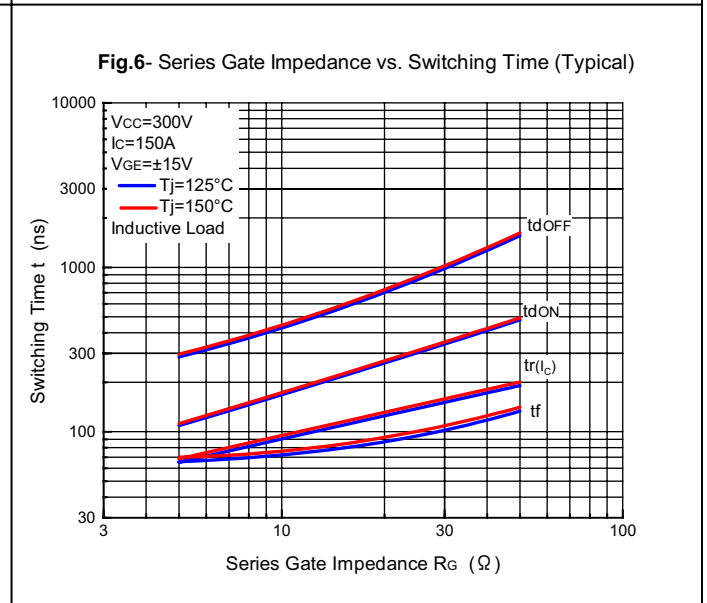
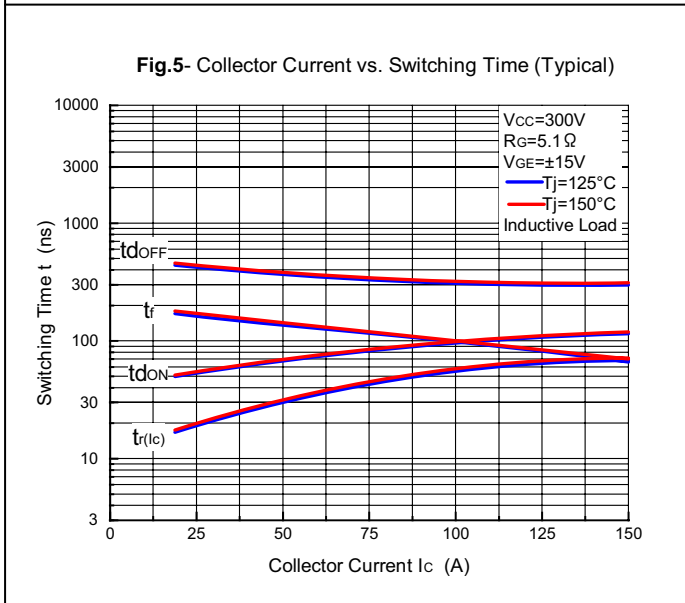
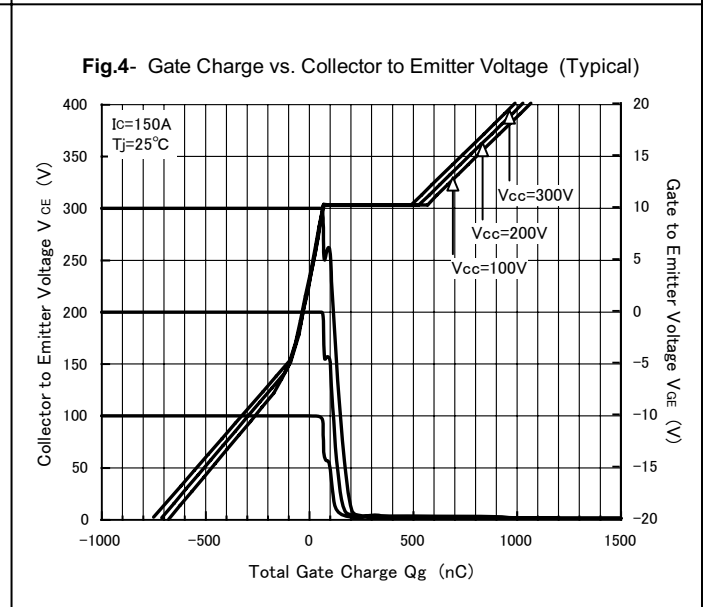
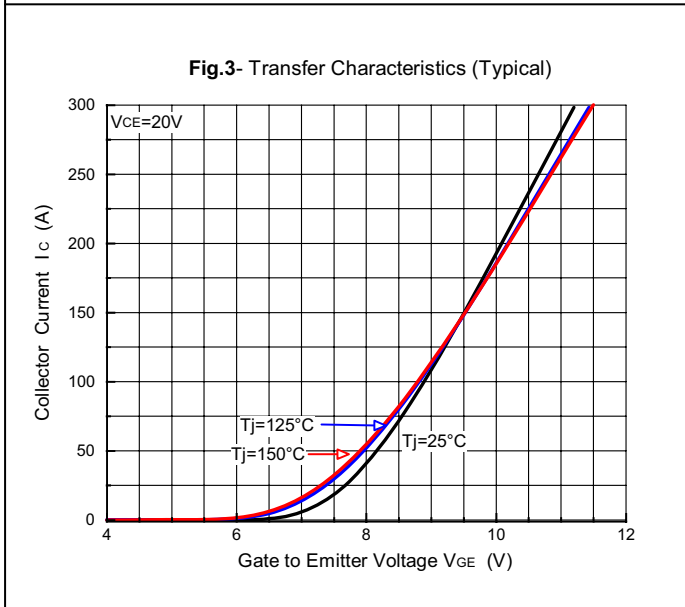
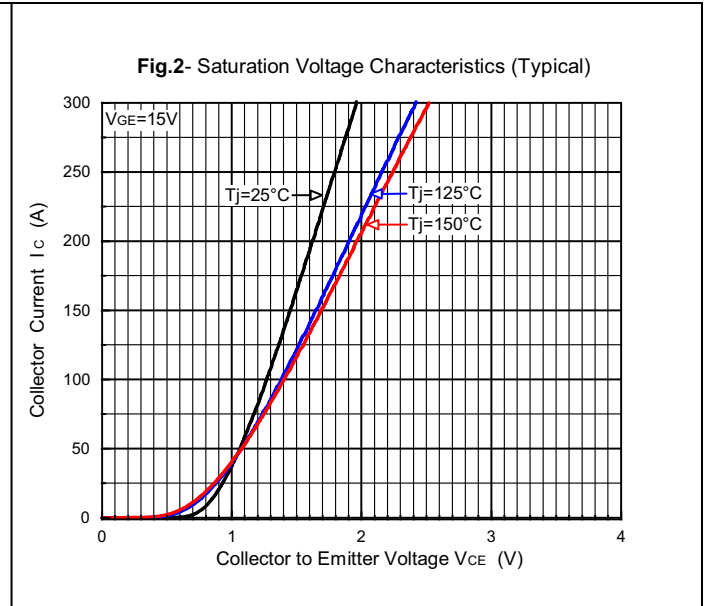
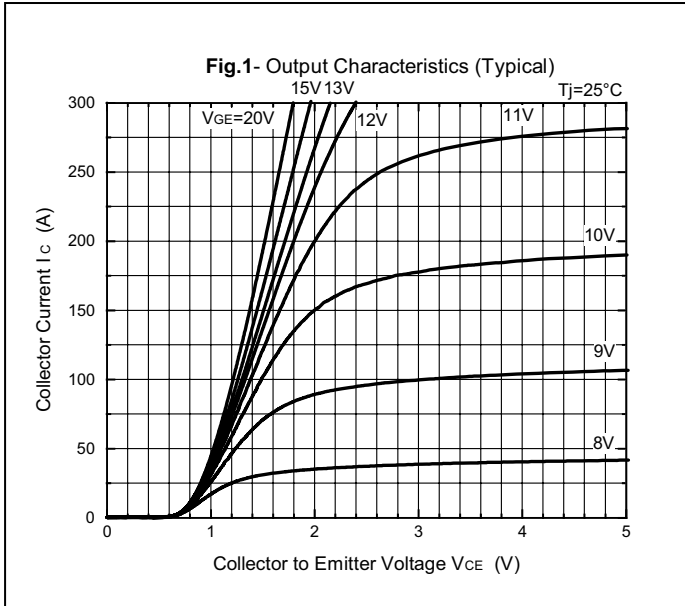
□ 電 氣 的 特 性 : **ELECTRICAL CHARACTERISTICS** (at $T_J=25^\circ\text{C}$ unless otherwise specified)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit	
IGBT	コレクタ遮断電流 Collector-Emitter Cut-Off Current	ICES	$V_{CE}=650\text{V}, V_{GE}=0\text{V}$	—	—	1.0	mA	
	ゲート漏れ電流 Gate-Emitter Leakage Current	IGES	$V_{GE}=\pm 20\text{V}, V_{CE}=0\text{V}$	—	—	1.0	μA	
	コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	VCE(sat.)	$I_c=150\text{A}, V_{GE}=15\text{V}$ (chip level)	$T_J=25^\circ\text{C}$	—	1.45	1.95	V
				$T_J=125^\circ\text{C}$	—	1.65	—	
				$T_J=150^\circ\text{C}$	—	1.70	—	
	ゲートしきい値電圧 Gate-Emitter Threshold Voltage	VGE(th.)	$V_{CE}=10\text{V}, I_c=3\text{mA}$	4.8	—	7.0	V	
	入力容量 Input Capacitance	Cies	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	—	12.5	—	nF	
	出力容量 Output Capacitance	Coes		—	0.5	—		
	帰還容量 Reverse Transfer Capacitance	Cres		—	0.4	—		
	ゲート電荷量 Gate Charge	Qg	$V_{CC}=300\text{V}, I_c=150\text{A}, V_{GE}=-15\sim+15\text{V}$	—	1275	—	nC	
スイッチング時間 Switching Time	上昇時間 Rise Time	tr	$V_{CC}=300\text{V}, L_s=38\text{nH}$ $I_c=150\text{A}$ Inductive Load $R_g=5.1\Omega$ $V_{GE}=\pm 15\text{V}$ $T_J=150^\circ\text{C}$	—	71	—	ns	
	ターンオン遅延時間 Turn-on Delay Time	td(on)		—	119	—		
	下降時間 Fall Time	tf		—	70	—		
	ターンオフ遅延時間 Turn-off Delay Time	td(off)		—	300	—		
順電圧 Peak Forward Voltage	VF	$I_f=150\text{A}, V_{GE}=0\text{V}$ (chip level)	$T_J=25^\circ\text{C}$	—	1.70	2.20	V	
			$T_J=125^\circ\text{C}$	—	1.60	—		
			$T_J=150^\circ\text{C}$	—	1.55	—		
逆回復時間 Reverse Recovery Time	trr	$V_{CC}=300\text{V}, L_s=38\text{nH}$ $I_c=150\text{A}$ Inductive Load $R_g=5.1\Omega$ $V_{GE}=\pm 15\text{V}$ $T_J=150^\circ\text{C}$	—	140	—	ns		
内部配線抵抗 Internal Lead Resistance	RCC+EE'	主端子—チップ間 / 1素子 Main Terminal - Chip / Per 1 Arm	—	—	1	m Ω		
内部インダクタンス Stray Inductance	LSCE	メイン端子3—2間 Main Terminal3 - Main Terminal2	—	30	—	nH		

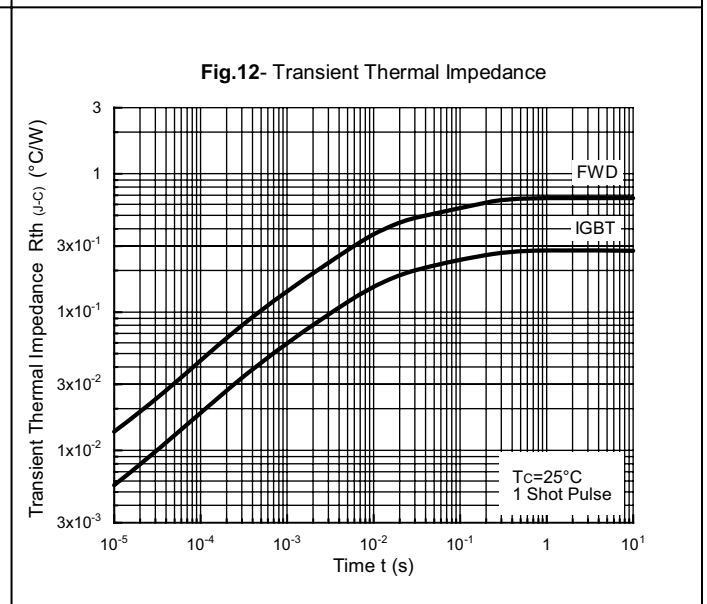
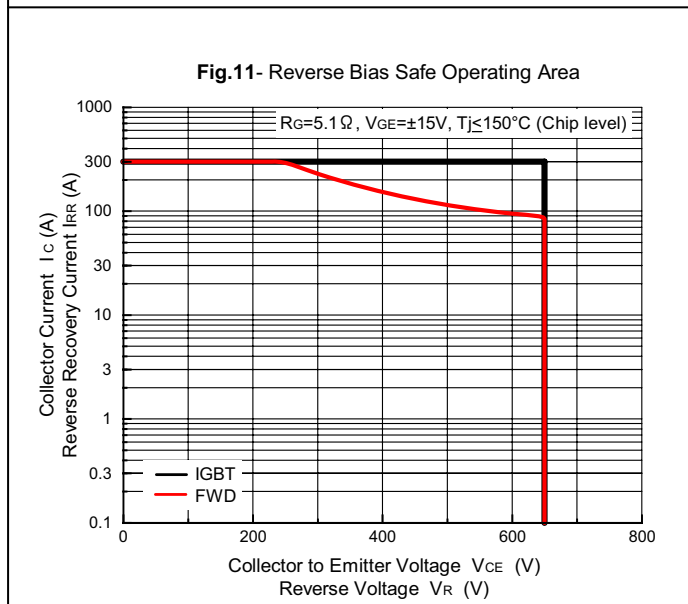
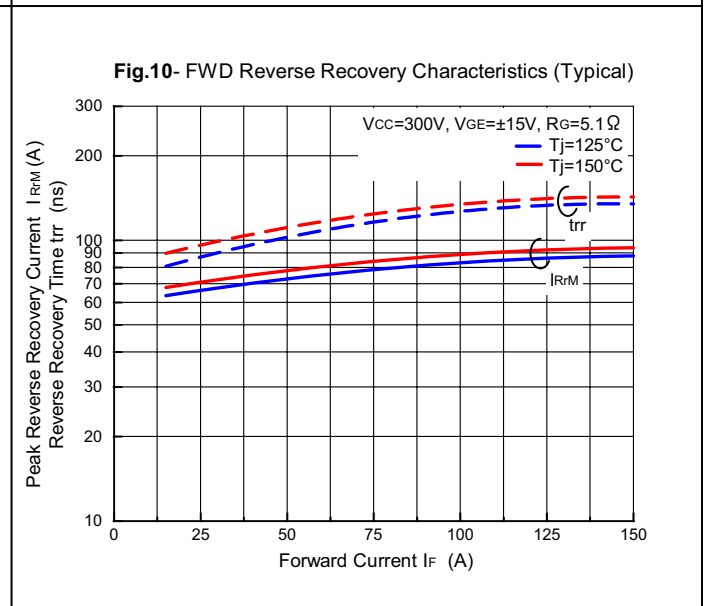
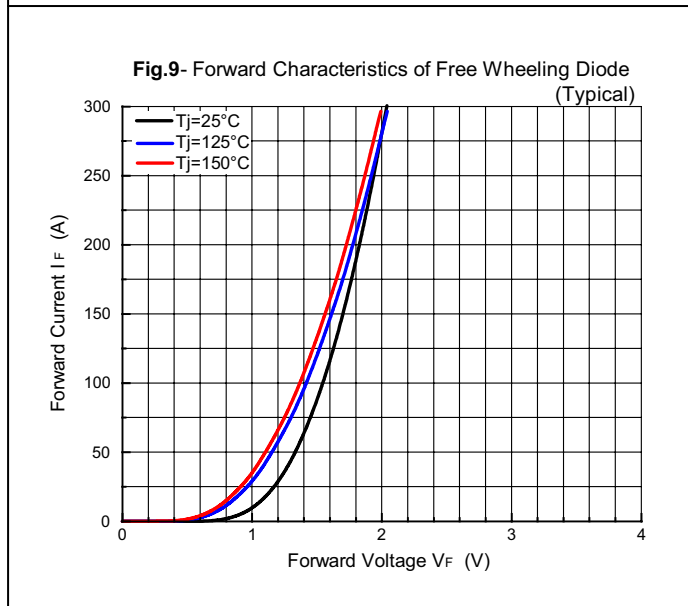
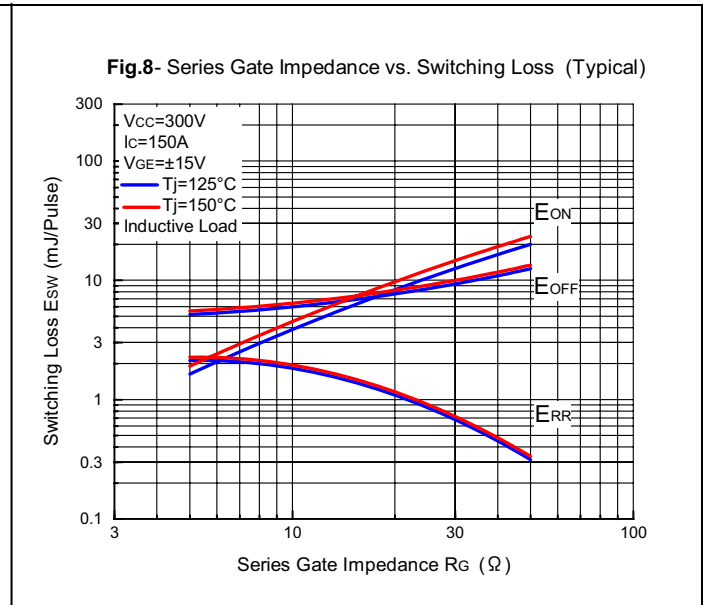
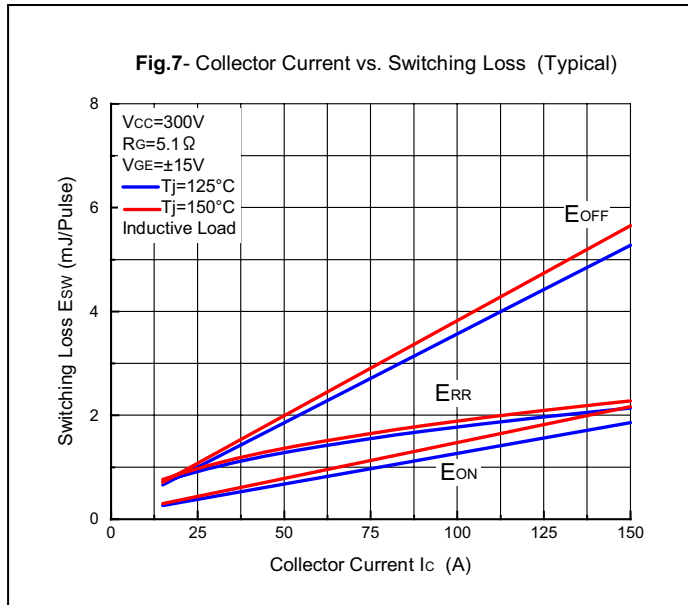
□ 熱 的 特 性 : **THERMAL CHARACTERISTICS**

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Resistance	IGBT	Rth(j-c)	Junction to Case Per 1 Arm (Tc測定点: チップ直下)	—	—	0.28	°C/W
	FWD			—	—	0.67	
接触熱抵抗 Thermal Resistance	IGBT	Rth(c-f)	Case to heatsink Per 1 Arm Paste=1W/(m ² °C)	—	0.10	—	
	FWD			—	0.17	—	

特性图 : CHARACTERISTICS CURVES



特性 : CHARACTERISTICS CURVES



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[KYOCERA AVX:](#)

[PRHMB150W6](#)